

## PJQ4401P

### 30V P-Channel Enhancement Mode MOSFET

**Voltage**    **-30 V**    **Current**    **-50 A**

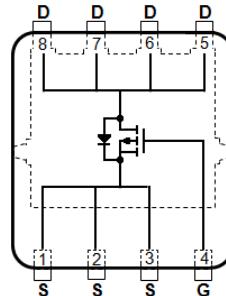
#### Features

- $R_{DS(ON)}$ ,  $V_{GS} @ -10V, I_D @ -10A < 8.5m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS} @ -4.5V, I_D @ -8A < 14m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams

DFN3333-8L



#### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-50	A
$T_c=100^\circ C$		-32	
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	-200	
Power Dissipation	$P_D$	60	W
$T_c=100^\circ C$		24	
Continuous Drain Current	$I_D$	-10	A
$T_A=70^\circ C$		-8	
Power Dissipation	$P_D$	2.0	W
$T_A=70^\circ C$		1.3	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150	°C
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{\theta JC}$	°C/W
	Junction to Ambient	$R_{\theta JA}$	

- Limited only By Maximum Junction Temperature

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## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=-250\mu\text{A}$	-30	-	-	V
Gate Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=-250\mu\text{A}$	-1.0	-1.5	-2.5	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS(on)}}$	$\text{V}_{\text{GS}}=-10\text{V}, \text{I}_D=-10\text{A}$	-	7.1	8.5	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_D=-8\text{A}$	-	10	14	
Zero Gate Voltage Drain Current	$\text{I}_{\text{DSS}}$	$\text{V}_{\text{DS}}=-30\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	-1.0	$\mu\text{A}$
Gate-Source Leakage Current	$\text{I}_{\text{GSS}}$	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	nA
<b>Dynamic</b> <sup>(Note 6)</sup>						
Total Gate Charge	$\text{Q}_g$	$\text{V}_{\text{DS}}=-15\text{V}, \text{I}_D=-10\text{A}, \text{V}_{\text{GS}}=-4.5\text{V}$ <sup>(Note 1,2)</sup>	-	27	-	nC
Gate-Source Charge	$\text{Q}_{\text{gs}}$		-	8.4	-	
Gate-Drain Charge	$\text{Q}_{\text{gd}}$		-	8.7	-	
Input Capacitance	$\text{C}_{\text{iss}}$	$\text{V}_{\text{DS}}=-15\text{V}, \text{V}_{\text{GS}}=0\text{V}, f=1.0\text{MHZ}$	-	3228	-	pF
Output Capacitance	$\text{C}_{\text{oss}}$		-	396	-	
Reverse Transfer Capacitance	$\text{Crss}$		-	254	-	
Turn-On Delay Time	$\text{t}_{\text{d(on)}}$	$\text{V}_{\text{DS}}=-15\text{V}, \text{ID}=-1\text{A}, \text{V}_{\text{GS}}=-10\text{V}, \text{R}_G=6\Omega$ <sup>(Note 1,2)</sup>	-	10	-	ns
Turn-On Rise Time	$\text{t}_r$		-	13	-	
Turn-Off Delay Time	$\text{t}_{\text{d(off)}}$		-	111	-	
Turn-Off Fall Time	$\text{t}_f$		-	51	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$\text{I}_s$	---	-	-	-50	A
Diode Forward Voltage	$\text{V}_{\text{SD}}$	$\text{I}_s=-1\text{A}, \text{V}_{\text{GS}}=0\text{V}$	-	-0.7	-1	V

### NOTES :

1. Pulse width $\leq 300\mu\text{s}$ , Duty cycle $\leq 2\%$ .
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature  $\text{T}_{\text{J(MAX)}}=150^\circ\text{C}$ . Ratings are based on low frequency and duty cycles to keep initial  $\text{T}_j = 25^\circ\text{C}$ .
4. The maximum current rating is package limited.
5.  $\text{R}_{\text{QJA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.

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## TYPICAL CHARACTERISTIC CURVES

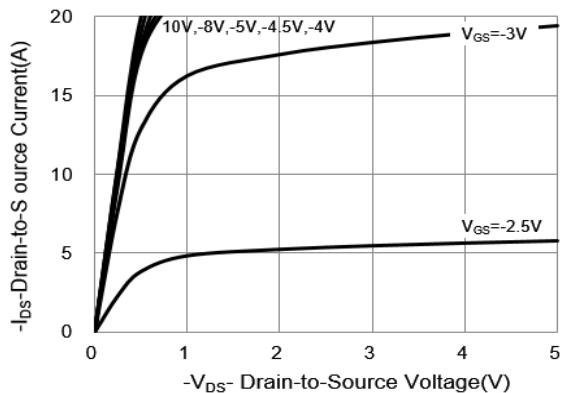


Fig.1 On-Region Characteristics

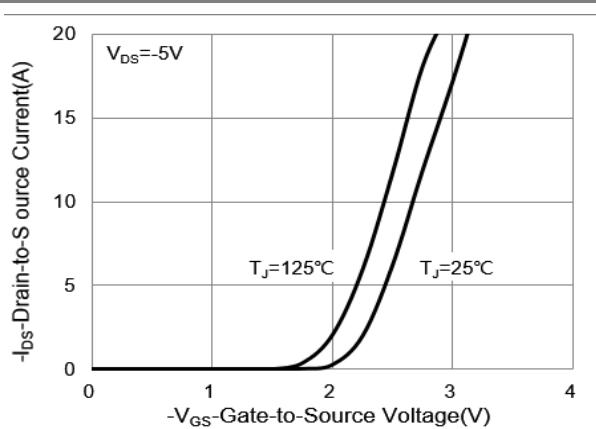


Fig.2 Transfer Characteristics

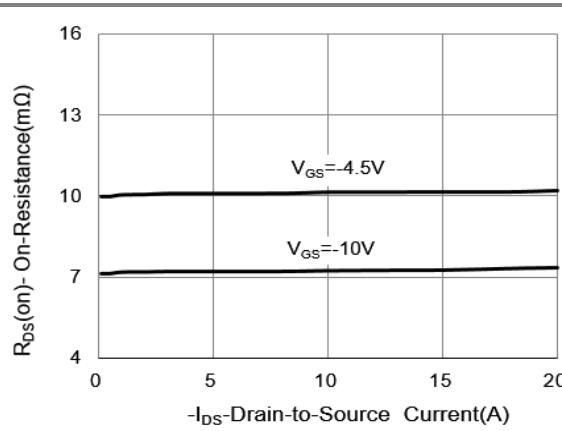


Fig.3 On-Resistance vs. Drain Current

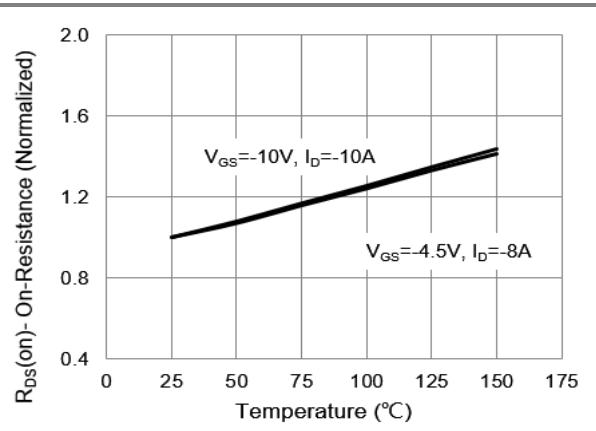


Fig.4 On-Resistance vs. Junction temperature

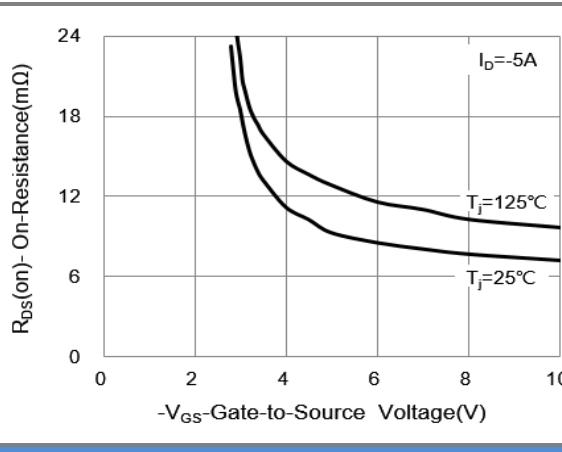


Fig.5 On-Resistance Variation with VGS.

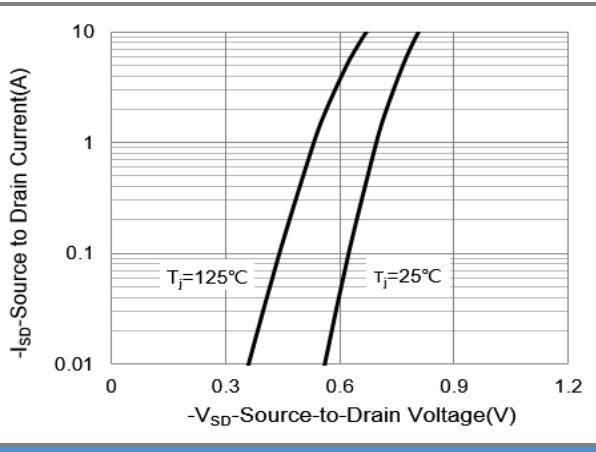


Fig.6 Source-Drain Diode Forward Voltage

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## TYPICAL CHARACTERISTIC CURVES

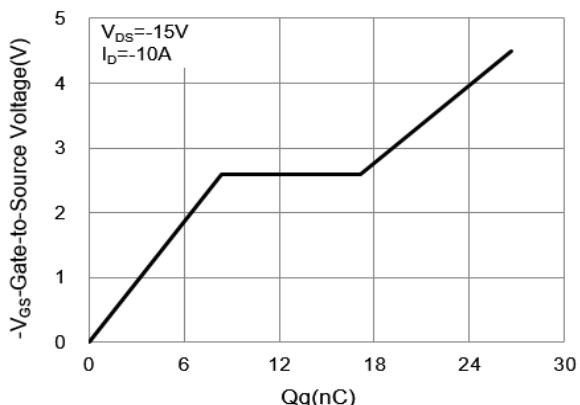


Fig.7 Gate-Charge Characteristics

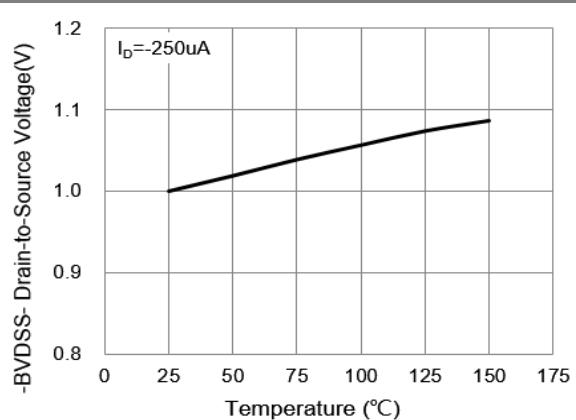


Fig.8 Breakdown Voltage Variation vs. Temperature.

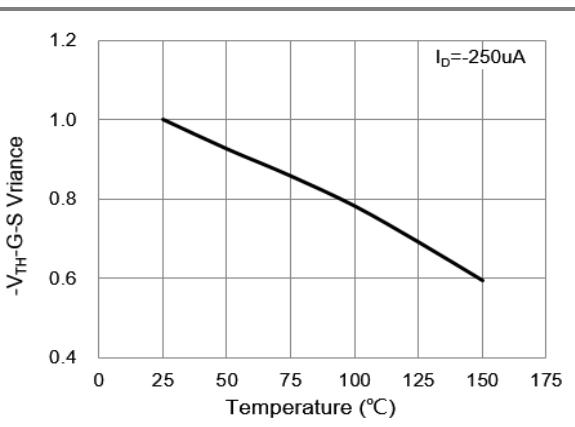


Fig.9 Threshold Voltage Variation with Temperature

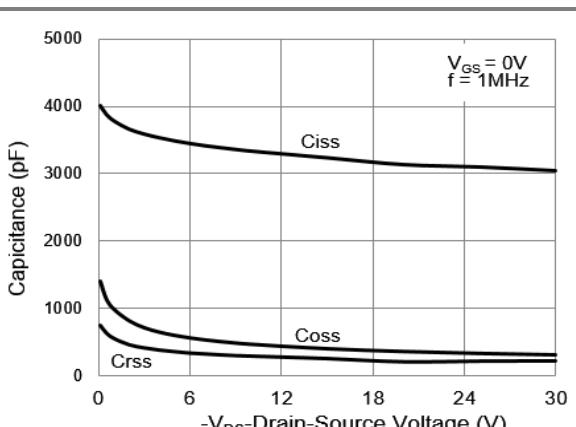


Fig.10 Capacitance vs. Drain-Source Voltage

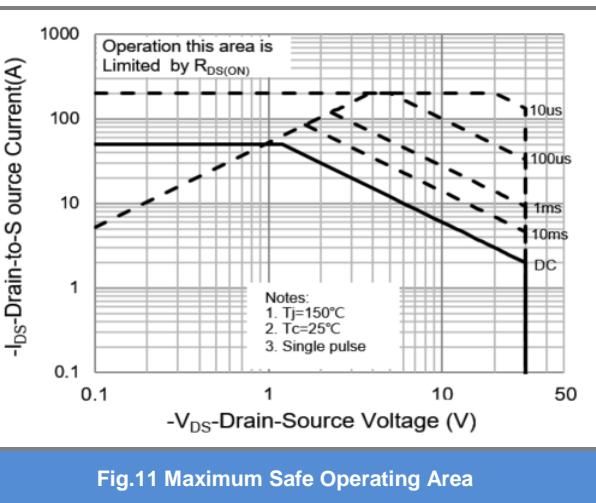


Fig.11 Maximum Safe Operating Area

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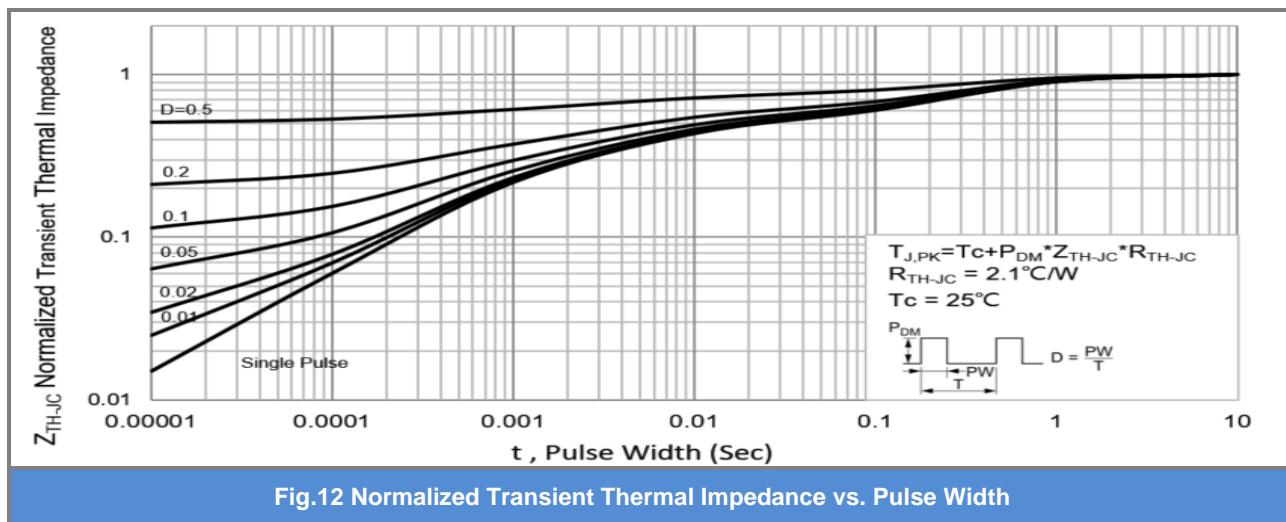


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

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## Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4401P_R2_00001	DFN3333-8L	5K pcs / 13" reel	4401	Halogen free RoHS compliant

## Packaging Information & Mounting Pad Layout

